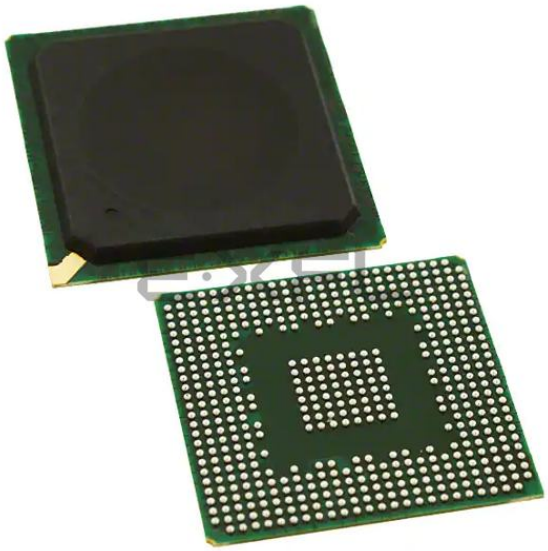

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

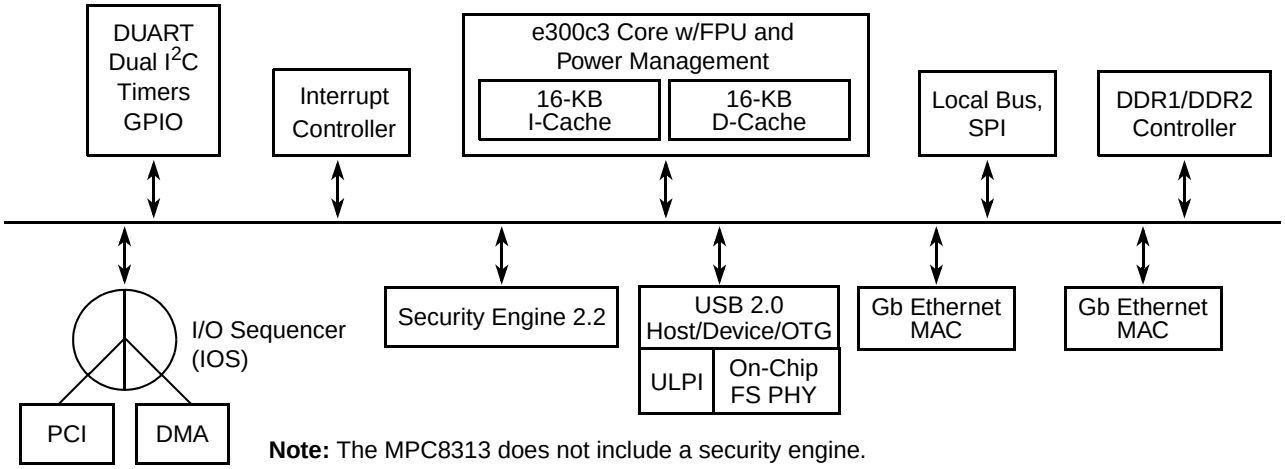
Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	267MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	516-BBGA Exposed Pad
Supplier Device Package	516-TEPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8313vraddb

1 Overview

The MPC8313E incorporates the e300c3 core, which includes 16 Kbytes of L1 instruction and data caches and on-chip memory management units (MMUs). The MPC8313E has interfaces to dual enhanced three-speed 10/100/1000 Mbps Ethernet controllers, a DDR1/DDR2 SDRAM memory controller, an enhanced local bus controller, a 32-bit PCI controller, a dedicated security engine, a USB 2.0 dual-role controller and an on-chip high-speed PHY, a programmable interrupt controller, dual I^2C controllers, a 4-channel DMA controller, and a general-purpose I/O port. This figure shows a block diagram of the MPC8313E.



Note: The MPC8313 does not include a security engine.

Figure 1. MPC8313E Block Diagram

The MPC8313E security engine (SEC 2.2) allows CPU-intensive cryptographic operations to be offloaded from the main CPU core. The security-processing accelerator provides hardware acceleration for the DES, 3DES, AES, SHA-1, and MD-5 algorithms.

1.1 MPC8313E Features

The following features are supported in the MPC8313E:

- Embedded PowerPC™ e300 processor core built on Power Architecture™ technology; operates at up to 333 MHz.
- High-performance, low-power, and cost-effective host processor
- DDR1/DDR2 memory controller—one 16-/32-bit interface at up to 333 MHz supporting both DDR1 and DDR2
- 16-Kbyte instruction cache and 16-Kbyte data cache, a floating point unit, and two integer units
- Peripheral interfaces such as 32-bit PCI interface with up to 66-MHz operation, 16-bit enhanced local bus interface with up to 66-MHz operation, and USB 2.0 (high speed) with an on-chip PHY.
- Security engine provides acceleration for control and data plane security protocols
- Power management controller for low-power consumption
- High degree of software compatibility with previous-generation PowerQUICC processor-based designs for backward compatibility and easier software migration

1.6 USB Dual-Role Controller

The MPC8313E USB controller includes the following features:

- Supports USB on-the-go mode, which includes both device and host functionality, when using an external ULPI (UTMI + low-pin interface) PHY
- Compatible with *Universal Serial Bus Specification, Rev. 2.0*
- Supports operation as a stand-alone USB device
  - Supports one upstream facing port
  - Supports three programmable USB endpoints
- Supports operation as a stand-alone USB host controller
  - Supports USB root hub with one downstream-facing port
  - Enhanced host controller interface (EHCI) compatible
- Supports high-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operation. Low-speed operation is supported only in host mode.
- Supports UTMI + low pin interface (ULPI) or on-chip USB 2.0 full-speed/high-speed PHY

1.7 Dual Enhanced Three-Speed Ethernet Controllers (eTSECs)

The MPC8313E eTSECs include the following features:

- Two RGMII/SGMII/MII/RMII/RTBI interfaces
- Two controllers designed to comply with IEEE Std 802.3®, 802.3u®, 802.3x®, 802.3z®, 802.3au®, and 802.3ab®
- Support for Wake-on-Magic Packet™, a method to bring the device from standby to full operating mode
- MII management interface for external PHY control and status
- Three-speed support (10/100/1000 Mbps)
- On-chip high-speed serial interface to external SGMII PHY interface
- Support for IEEE Std 1588™
- Support for two full-duplex FIFO interface modes
- Multiple PHY interface configuration
- TCP/IP acceleration and QoS features available
- IP v4 and IP v6 header recognition on receive
- IP v4 header checksum verification and generation
- TCP and UDP checksum verification and generation
- Per-packet configurable acceleration
- Recognition of VLAN, stacked (queue in queue) VLAN, IEEE Std 802.2®, PPPoE session, MPLS stacks, and ESP/AH IP-security headers
- Transmission from up to eight physical queues.
- Reception to up to eight physical queues

1.10 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) allows the MPC8313E to exchange data between other PowerQUICC family chips, Ethernet PHYs for configuration, and peripheral devices such as EEPROMs, real-time clocks, A/D converters, and ISDN devices.

The SPI is a full-duplex, synchronous, character-oriented channel that supports a four-wire interface (receive, transmit, clock, and slave select). The SPI block consists of transmitter and receiver sections, an independent baud-rate generator, and a control unit.

1.11 DMA Controller, Dual I^2C, DUART, Local Bus Controller, and Timers

The MPC8313E provides an integrated four-channel DMA controller with the following features:

- Allows chaining (both extended and direct) through local memory-mapped chain descriptors (accessible by local masters)
- Supports misaligned transfers

There are two I^2C controllers. These synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. The 16-byte FIFOs are supported for both the transmitter and the receiver.

The MPC8313E local bus controller (LBC) port allows connections with a wide variety of external DSPs and ASICs. Three separate state machines share the same external pins and can be programmed separately to access different types of devices. The general-purpose chip select machine (GPCM) controls accesses to asynchronous devices using a simple handshake protocol. The three user programmable machines (UPMs) can be programmed to interface to synchronous devices or custom ASIC interfaces. Each chip select can be configured so that the associated chip interface can be controlled by the GPCM or UPM controller. The FCM provides a glueless interface to parallel-bus NAND Flash E2PROM devices. The FCM contains three basic configuration register groups—BR*n*, OR*n*, and FMR. Both may exist in the same system. The local bus can operate at up to 66 MHz.

The MPC8313E system timers include the following features: periodic interrupt timer, real time clock, software watchdog timer, and two general-purpose timer blocks.

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8313E. The MPC8313E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

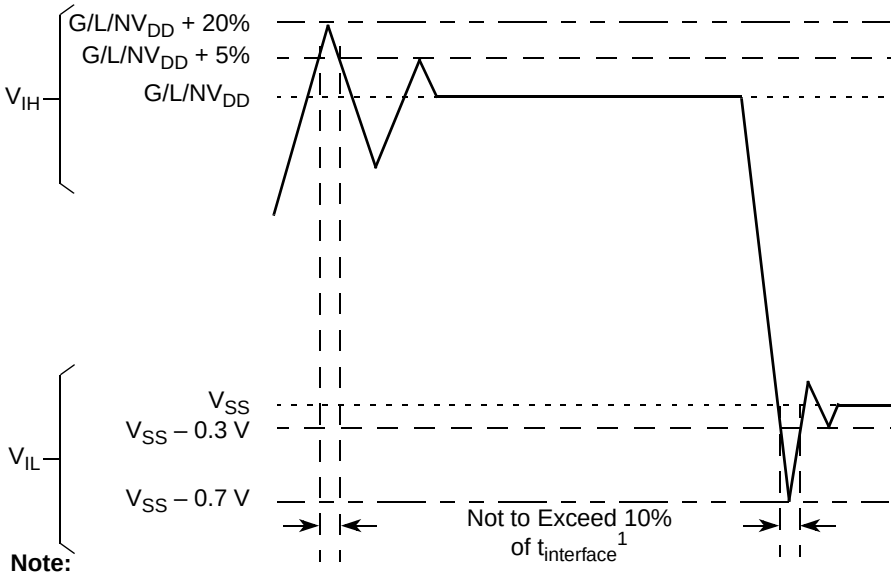
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value[1]	Unit	Current Requirement

Note:

1. GV_{DD}, NV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. Some GPIO pins may operate from a 2.5-V supply when configured for other functions.
3. Min temperature is specified with T_A; Max temperature is specified with T_J.
4. All Power rails must be connected and power applied to the MPC8313 even if the IP interfaces are not used.
5. All I/O pins should be interfaced with peripherals operating at same voltage level.
6. This voltage is the input to the filter discussed in Section 22.2, "PLL Power Supply Filtering" and not necessarily the voltage at the AVDD pin, which may be reduced from VDD by the filter.

This figure shows the undershoot and overshoot voltages at the interfaces of the MPC8313E.



Note:

1. Note that $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/NV_{DD}/LV_{DD}

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	NV_{DD} = 3.3 V
PCI signals	25	
DDR signal	18	GV_{DD} = 2.5 V

3 Power Characteristics

The estimated typical power dissipation, not including I/O supply power, for this family of MPC8313E devices is shown in this table. Table 5 shows the estimated typical I/O power dissipation.

Table 4. MPC8313E Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	Typical[2]	Maximum for Rev. 1.0 Silicon[3]	Maximum for Rev. 2.x or Later Silicon[3]	Unit
333	167	820	1020	1200	mW
400	133	820	1020	1200	mW

Note:

1. The values do not include I/O supply power or AV_{DD}, but do include core, USB PLL, and a portion of SerDes digital power (not including $XCOREV_{DD}$, $XPADV_{DD}$, or $SDAV_{DD}$, which all have dedicated power supplies for the SerDes PHY).
2. Typical power is based on a voltage of V_{DD} = 1.05 V and an artificial smoker test running at room temperature.
3. Maximum power is based on a voltage of V_{DD} = 1.05 V, a junction temperature of T_J = 105°C, and an artificial smoker test.

This table describes a typical scenario where blocks with the stated percentage of utilization and impedances consume the amount of power described.

Table 5. MPC8313E Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	NV_{DD} (3.3 V)	LV_{DDA}/ LV_{DDB} (3.3 V)	LV_{DDA}/ LV_{DDB} (2.5 V)	LV_{DD} (3.3 V)	Unit	Comments
DDR 1, 60% utilization, 50% read/write R_s = 22 Ω R_t = 50 Ω single pair of clock capacitive load: data = 8 pF, control address = 8 pF, clock = 8 pF	333 MHz, 32 bits	—	0.355	—	—	—	—	W	—
	266 MHz, 32 bits	—	0.323	—	—	—	—	W	—
DDR 2, 60% utilization, 50% read/write R_s = 22 Ω R_t = 75 Ω single pair of clock capacitive load: data = 8 pF, control address = 8 pF, clock = 8 pF	333 MHz, 32 bits	0.266	—	—	—	—	—	W	—
	266 MHz, 32 bits	0.246	—	—	—	—	—	W	—
PCI I/O load = 50 pF	33 MHz	—	—	0.120	—	—	—	W	—
	66 MHz	—	—	0.249	—	—	—	W	—
Local bus I/O load = 20 pF	66 MHz	—	—	—	—	—	0.056	W	—
	50 MHz	—	—	—	—	—	0.040	W	—
TSEC I/O load = 20 pF	MII, 25 MHz	—	—	—	0.008	—	—	W	Multiple by number of interface used
	RGMII, 125 MHz	—	—	—	0.078	0.044	—	W	

Table 5. MPC8313E Typical I/O Power Dissipation (continued)

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	NV_{DD} (3.3 V)	LV_{DDA}/ LV_{DDB} (3.3 V)	LV_{DDA}/ LV_{DDB} (2.5 V)	LV_{DD} (3.3 V)	Unit	Comments
USBDR controller load = 20 pF	60 MHz	—	—	—	0.078	—	—	W	—
Other I/O	—	—	—	0.015	—	—	—	W	—

This table shows the estimated core power dissipation of the MPC8313E while transitioning into the D3 warm low-power state.

Table 6. MPC8313E Low-Power Modes Power Dissipation[1]

333-MHz Core, 167-MHz CSB[2]	Rev. 1.0[3]	Rev. 2.x or Later[3]	Unit
D3 warm	400	425	mW

Note:

1. All interfaces are enabled. For further power savings, disable the clocks to unused blocks.
2. The interfaces are run at the following frequencies: DDR: 333 MHz, eLBC 83 MHz, PCI 33 MHz, eTSEC1 and TSEC2: 167 MHz, SEC: 167 MHz, USB: 167 MHz. See the SCCR register for more information.
3. This is maximum power in D3 Warm based on a voltage of 1.05 V and a junction temperature of 105°C.

4 Clock Input Timing

This section provides the clock input DC and AC electrical characteristics for the MPC8313E.

4.1 DC Electrical Characteristics

This table provides the system clock input (SYS_CLK_IN/PCI_SYNC_IN) DC timing specifications for the MPC8313E.

Table 7. SYS_CLK_IN DC Electrical Characteristics

Parameter	Condition	Symbol	Min	Max	Unit
Input high voltage	—	V_{IH}	2.4	NV_{DD} + 0.3	V
Input low voltage	—	V_{IL}	–0.3	0.4	V
SYS_CLK_IN input current	$0 V \le V_{IN} \le NV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0 V \le V_{IN} \le 0.5 V$ or $NV_{DD} – 0.5 V \le V_{IN} \le NV_{DD}$	I_{IN}	—	±10	μA
PCI_SYNC_IN input current	$0.5 V \le V_{IN} \le NV_{DD} – 0.5 V$	I_{IN}	—	±50	μA

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications for Rev. 1.0 Silicon

Parameter	Symbol [1]	Min	Max	Unit	Note
MCK[*n*] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	6	10	ns	2
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHAS}	 2.1 2.5	 — —	ns	3
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHAX}	 2.4 3.15	 — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHCS}	 2.4 3.15	 — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHCX}	 2.4 3.15	 — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 333 MHz 266 MHz	t_{DDKHDS}, t_{DDKLDS}	 800 900	 — —	ps	5
MDQ//MDM output hold with respect to MDQS 333 MHz 266 MHz	t_{DDKHDX}, t_{DDKLDX}	 900 1100	 — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ//MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual,* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Silicon Rev 2.x or Later

Parameter	Symbol[1]	Min	Max	Unit	Note
MCK[*n*] cycle time, MCK[*n*]/$\overline{\text{MCK}}$[*n*] crossing	t_{MCK}	6	10	ns	2
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHAS}	 2.1 2.5	 — —	ns	3
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHAX}	 2.0 2.7	 — —	ns	3
$\overline{\text{MCS}}$[*n*] output setup with respect to MCK 333 MHz 266 MHz	t_{DDKHCS}	 2.1 3.15	 — —	ns	3
$\overline{\text{MCS}}$[*n*] output hold with respect to MCK 333 MHz 266 MHz	t_{DDKHCX}	 2.0 2.7	 — —	ns	3
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 333 MHz 266 MHz	t_{DDKHDS}, t_{DDKLDS}	 800 900	 — —	ps	5
MDQ//MDM output hold with respect to MDQS 333 MHz 266 MHz	t_{DDKHDX}, t_{DDKLDX}	 750 1000	 — —	ps	5
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ//MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual,* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

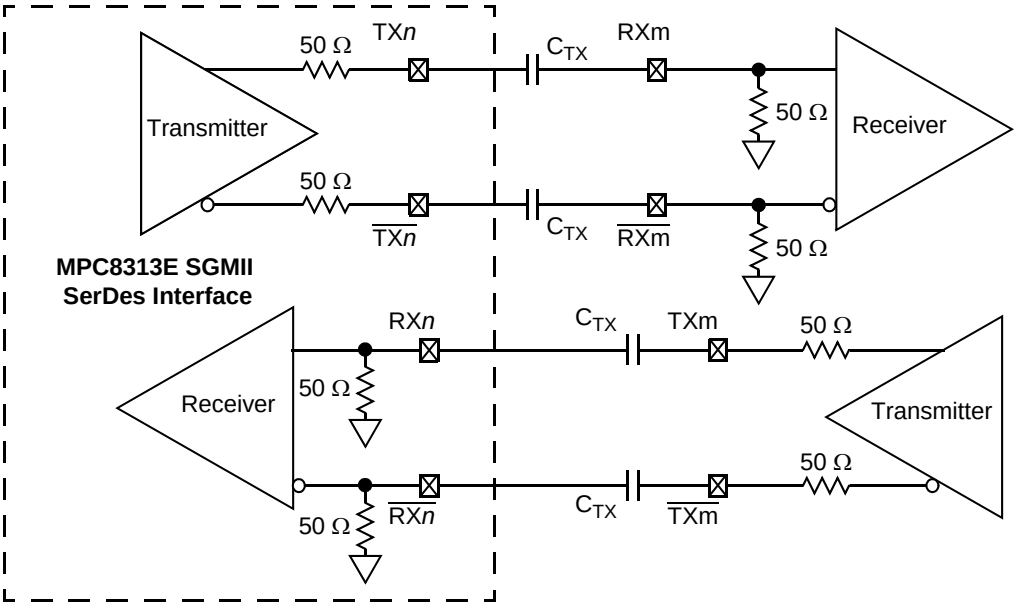


Figure 15. 4-Wire AC-Coupled SGMII Serial Link Connection Example

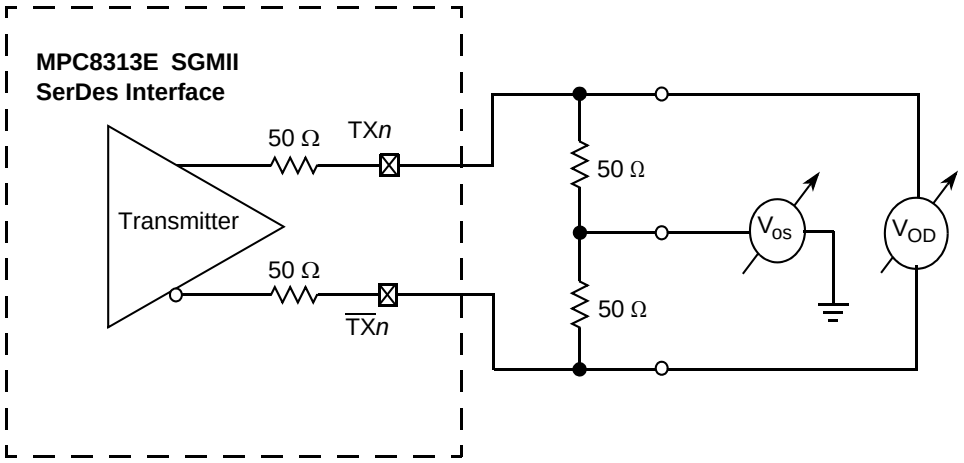


Figure 16. SGMII Transmitter DC Measurement Circuit

Table 33. SGMII DC Receiver Electrical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	$XCOREV_{DD}$	0.95	1.0	1.05	V	
DC Input voltage range			N/A			1
Input differential voltage	$V_{RX\_DIFFp\text{-}p}$	100	—	1200	mV	2
Loss of signal threshold	VL_{OS}	30	—	100	mV	
Input AC common mode voltage	$V_{CM\_ACp\text{-}p}$	—	—	100	mV	3
Receiver differential input impedance	Z_{RX_DIFF}	80	100	120	Ω	
Receiver common mode input impedance	Z_{RX_CM}	20	—	35	Ω	

Table 33. SGMII DC Receiver Electrical Characteristics (continued)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Common mode input voltage	V_{CM}	—	$V_{xcorevss}$	—	V	4

Notes:
1. Input must be externally AC-coupled.
2. $V_{RX\_DIFFp\text{-}p}$ is also referred to as peak to peak input differential voltage
3. $V_{CM\_ACp\text{-}p}$ is also referred to as peak to peak AC common mode voltage.
4. On-chip termination to $XCOREV_{SS}$.

8.3.4 SGMII AC Timing Specifications

This section describes the SGMII transmit and receive AC timing specifications. Transmitter and receiver characteristics are measured at the transmitter outputs (TX[*n*] and $\overline{\text{TX}}$[*n*]) or at the receiver inputs (RX[*n*] and $\overline{\text{RX}}$[*n*]) as depicted in Figure 18, respectively.

8.3.4.1 SGMII Transmit AC Timing Specifications

This table provides the SGMII transmit AC timing targets. A source synchronous clock is not provided.

Table 34. SGMII Transmit AC Timing Specifications

At recommended operating conditions with $XCOREV_{DD}$ = 1.0 V ± 5%.

Parameter	Symbol	Min	Typ	Max	Unit	Note
Deterministic jitter	JD	—	—	0.17	UI p-p	
Total jitter	JT	—	—	0.35	UI p-p	
Unit interval	UI	799.92	800	800.08	ps	1
V_{OD} fall time (80%–20%)	tfall	50	—	120	ps	
V_{OD} rise time (20%–80%)	t_{rise}	50	—	120	ps	

Note:
1. Each UI is 800 ps ± 100 ppm.

8.3.4.2 SGMII Receive AC Timing Specifications

This table provides the SGMII receive AC timing specifications. Source synchronous clocking is not supported. Clock is recovered from the data. Figure 17 shows the SGMII receiver input compliance mask eye diagram.

Table 35. SGMII Receive AC Timing Specifications

At recommended operating conditions with $XCOREV_{DD}$ = 1.0 V ± 5%.

Parameter	Symbol	Min	Typ	Max	Unit	Note
Deterministic jitter tolerance	JD	0.37	—	—	UI p-p	1
Combined deterministic and random jitter tolerance	JDR	0.55	—	—	UI p-p	1
Sinusoidal jitter tolerance	JSIN	0.1	—	—	UI p-p	1

assumes that the LVPECL clock driver's output impedance is 50 Ω. R1 is used to DC-bias the LVPECL outputs prior to AC coupling. Its value could be ranged from 140 to 240 Ω depending on the clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50-Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the MPC8313E SerDes3 reference clock's differential input amplitude requirement (between 200 and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω. Consult with the clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.

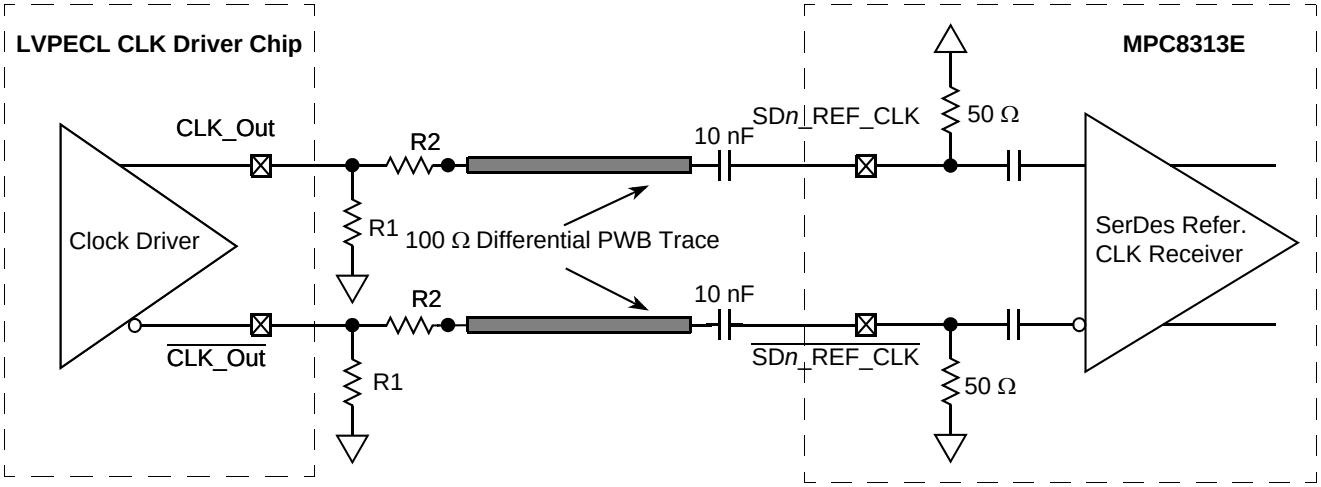


Figure 29. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

This figure shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with the MPC8313E SerDes reference clock input's DC requirement.

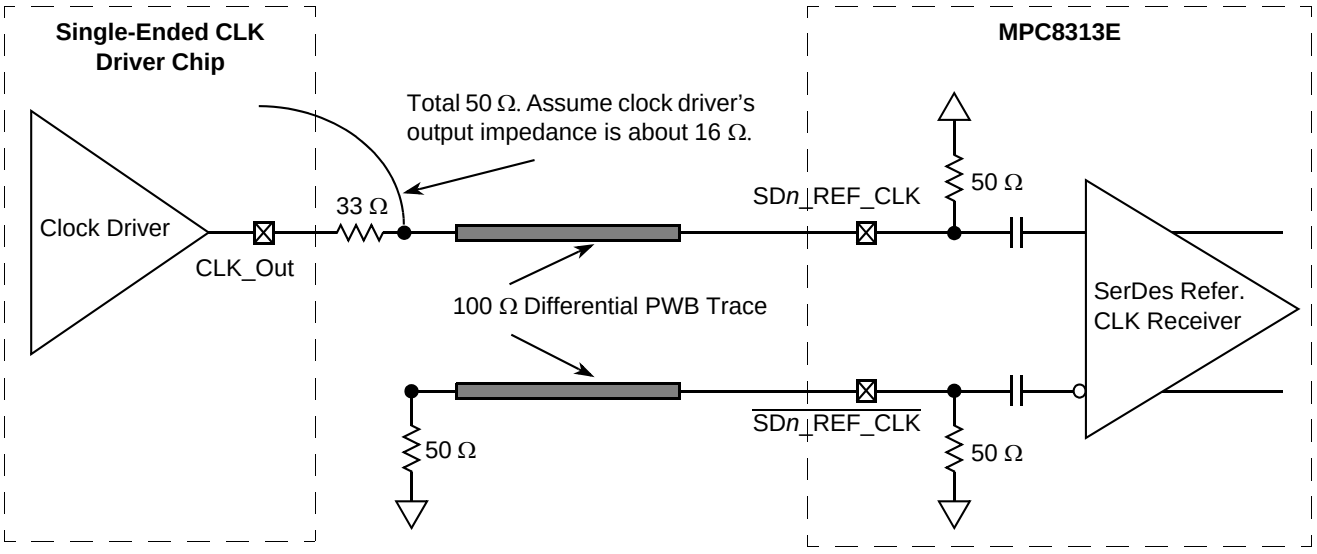


Figure 30. Single-Ended Connection (Reference Only)

9.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low-phase noise and cycle-to-cycle jitter. Phase noise less than 100 kHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise occurs in the 1–15 MHz range. The source impedance of the clock driver should be 50 Ω to match the transmission line and reduce reflections which are a source of noise to the system.

This table describes some AC parameters for SGMII protocol.

Table 39. SerDes Reference Clock Common AC Parameters

At recommended operating conditions with XV_{DD_SRDS1} or XV_{DD_SRDS2} = 1.0 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Note
Rising edge rate	Rise edge rate	1.0	4.0	V/ns	2, 3
Falling edge rate	Fall edge rate	1.0	4.0	V/ns	2, 3
Differential input high voltage	V_{IH}	+200	—	mV	2
Differential input low voltage	V_{IL}	—	–200	mV	2
Rising edge rate (SDn_REF_CLK) to falling edge rate ($\overline{\text{SDn\_REF\_CLK}}$) matching	Rise-fall matching	—	20	%	1, 4

Notes:
1. Measurement taken from single-ended waveform.
2. Measurement taken from differential waveform.
3. Measured from –200 to +200 mV on the differential waveform (derived from SD*n*_REF_CLK minus $\overline{\text{SD}n\text{\_REF\_CLK}}$). The signal must be monotonic through the measurement region for rise and fall time. The 400 mV measurement window is centered on the differential zero crossing. See Figure 31.
4. Matching applies to rising edge rate for SD*n*_REF_CLK and falling edge rate for $\overline{\text{SD}n\text{\_REF\_CLK}}$. It is measured using a 200 mV window centered on the median cross point, where SD*n*_REF_CLK rising meets $\overline{\text{SD}n\text{\_REF\_CLK}}$ falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of SD*n*_REF_CLK should be compared to the fall edge rate of $\overline{\text{SD}n\text{\_REF\_CLK}}$, the maximum allowed difference should not exceed 20% of the slowest edge rate. See Figure 32.

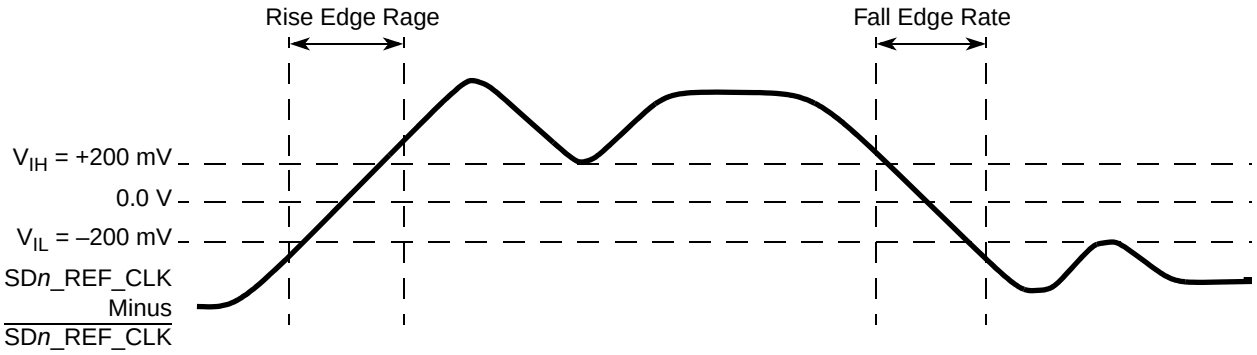


Figure 31. Differential Measurement Points for Rise and Fall Time

Table 60. SPI DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.1	NV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le NV_{DD}$	—	±5	μA

18.2 SPI AC Timing Specifications

This table and provide the SPI input and output AC timing specifications.

Table 61. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Note:

1. Output specifications are measured from the 50% level of the rising edge of SYS_CLK_IN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

This figure provides the AC test load for the SPI.

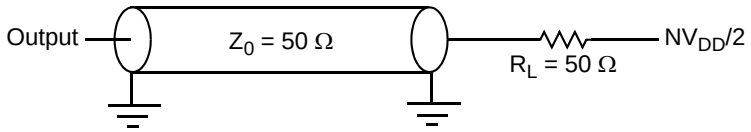


Figure 53. SPI AC Test Load

Figure 54 and Figure 55 represent the AC timing from Table 61. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
PCI_AD6	AD19	I/O	NV_{DD}	—
PCI_AD7	AD20	I/O	NV_{DD}	—
PCI_AD8	AC18	I/O	NV_{DD}	—
PCI_AD9	AD18	I/O	NV_{DD}	—
PCI_AD10	AB18	I/O	NV_{DD}	—
PCI_AD11	AE19	I/O	NV_{DD}	—
PCI_AD12	AB17	I/O	NV_{DD}	—
PCI_AD13	AE18	I/O	NV_{DD}	—
PCI_AD14	AD17	I/O	NV_{DD}	—
PCI_AD15	AF19	I/O	NV_{DD}	—
PCI_AD16	AB14	I/O	NV_{DD}	—
PCI_AD17	AF15	I/O	NV_{DD}	—
PCI_AD18	AD14	I/O	NV_{DD}	—
PCI_AD19	AE14	I/O	NV_{DD}	—
PCI_AD20	AF12	I/O	NV_{DD}	—
PCI_AD21	AE11	I/O	NV_{DD}	—
PCI_AD22	AD12	I/O	NV_{DD}	—
PCI_AD23	AB13	I/O	NV_{DD}	—
PCI_AD24	AF9	I/O	NV_{DD}	—
PCI_AD25	AD11	I/O	NV_{DD}	—
PCI_AD26	AE10	I/O	NV_{DD}	—
PCI_AD27	AB12	I/O	NV_{DD}	—
PCI_AD28	AD10	I/O	NV_{DD}	—
PCI_AD29	AC10	I/O	NV_{DD}	—
PCI_AD30	AF10	I/O	NV_{DD}	—
PCI_AD31	AF8	I/O	NV_{DD}	—
PCI_C/$\overline{BE0}$	AC19	I/O	NV_{DD}	—
PCI_C/$\overline{BE1}$	AB15	I/O	NV_{DD}	—
PCI_C/$\overline{BE2}$	AF14	I/O	NV_{DD}	—
PCI_C/$\overline{BE3}$	AF11	I/O	NV_{DD}	—
PCI_PAR	AD16	I/O	NV_{DD}	—
$\overline{PCI\_FRAME}$	AF16	I/O	NV_{DD}	5

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
TSEC1_TXD1/TSEC_1588_PP2	AD6	O	LV_{DDB}	—
TSEC1_TXD0/USBDR_STP/TSEC_1588_PP3	AD5	O	LV_{DDB}	—
TSEC1_TX_EN/TSEC_1588_ALARM1	AB7	O	LV_{DDB}	—
TSEC1_TX_ER/TSEC_1588_ALARM2	AB8	O	LV_{DDB}	—
TSEC1_GTX_CLK125	AE1	I	LV_{DDB}	—
TSEC1_MDC/LB_POR_CFG_BOOT_ECC_DIS	AF6	O	NV_{DD}	9, 11
TSEC1_MDIO	AB9	I/O	NV_{DD}	—
ETSEC2				
TSEC2_COL/GTM1_TIN4/GTM2_TIN3/GPIO15	AB4	I/O	LV_{DDA}	—
TSEC2_CRS/$\overline{\text{GTM1\_TGATE4}}$/$\overline{\text{GTM2\_TGATE3}}$/GPIO16	AB3	I/O	LV_{DDA}	—
TSEC2_GTX_CLK/$\overline{\text{GTM1\_TOUT4}}$/$\overline{\text{GTM2\_TOUT3}}$/GPIO17	AC1	I/O	LV_{DDA}	12
TSEC2_RX_CLK/GTM1_TIN2/GTM2_TIN1/GPIO18	AC2	I/O	LV_{DDA}	—
TSCE2_RX_DV/$\overline{\text{GTM1\_TGATE2}}$/$\overline{\text{GTM2\_TGATE1}}$/GPIO19	AA3	I/O	LV_{DDA}	—
TSEC2_RXD3/GPIO20	Y5	I/O	LV_{DDA}	—
TSEC2_RXD2/GPIO21	AA4	I/O	LV_{DDA}	—
TSEC2_RXD1/GPIO22	AB2	I/O	LV_{DDA}	—
TSEC2_RXD0/GPIO23	AA5	I/O	LV_{DDA}	—
TSEC2_RX_ER/$\overline{\text{GTM1\_TOUT2}}$/$\overline{\text{GTM2\_TOUT1}}$/GPIO24	AA2	I/O	LV_{DDA}	—
TSEC2_TX_CLK/GPIO25	AB1	I/O	LV_{DDA}	—
TSEC2_TXD3/CFG_RESET_SOURCE0	W3	I/O	LV_{DDA}	—
TSEC2_TXD2/CFG_RESET_SOURCE1	Y1	I/O	LV_{DDA}	—
TSEC2_TXD1/CFG_RESET_SOURCE2	W5	I/O	LV_{DDA}	—
TSEC2_TXD0/CFG_RESET_SOURCE3	Y3	I/O	LV_{DDA}	—
TSEC2_TX_EN/GPIO26	AA1	I/O	LV_{DDA}	—
TSEC2_TX_ER/GPIO27	W1	I/O	LV_{DDA}	—
SGMII PHY				
TXA	U3	O		—
$\overline{\text{TXA}}$	V3	O		—
RXA	U1	I		—
$\overline{\text{RXA}}$	V1	I		—
TXB	P4	O		—
$\overline{\text{TXB}}$	N4	O		—

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
RXB	R1	I		—
$\overline{\text{RXB}}$	P1	I		—
SD_IMP_CAL_RX	V5	I		200 Ω ± 10% to GND
$\overline{\text{SD\_REF\_CLK}}$	T5	I		—
SD_REF_CLK	T4	I		—
SD_PLL_TPD	T2	O		—
SD_IMP_CAL_TX	N5	I		100 Ω ± 10% to GND
SDAVDD	R5	I/O		—
SD_PLL_TPA_ANA	R4	O		—
SDAVSS	R3	I/O		—
USB PHY				
USB_DP	P26	I/O		—
USB_DM	N26	I/O		—
USB_VBUS	P24	I/O		—
USB_TPA	L26	I/O		—
USB_RBIAS	M24	I/O		—
USB_PLL_PWR3	M26	I/O		—
USB_PLL_GND	N24	I/O		—
USB_PLL_PWR1	N25	I/O		—
USB_VSSA_BIAS	M25	I/O		—
USB_VDDA_BIAS	M22	I/O		—
USB_VSSA	N22	I/O		—
USB_VDDA	P22	I/O		—
GTM/USB				
USBDR_DRIVE_VBUS/GTM1_TIN1/GTM2_TIN2/LSRCID0	AD23	I/O	NV_{DD}	—
USBDR_PWRFAULT/$\overline{\text{GTM1\_TGATE1}}$/$\overline{\text{GTM2\_TGATE2}}$/ LSRCID1	AE23	I/O	NV_{DD}	—
USBDR_PCTL0/$\overline{\text{GTM1\_TOUT1}}$/LSRCID2	AC22	O	NV_{DD}	—
USBDR_PCTL1/LBC_PM_REF_10/LSRCID3	AB21	O	NV_{DD}	—

Table 63. Configurable Clock Units

Unit	Default Frequency	Options
TSEC1	*csb_clk*	Off, *csb_clk*, *csb_clk*/2, *csb_clk*/3
TSEC2	*csb_clk*	Off, *csb_clk*, *csb_clk*/2, *csb_clk*/3
Security Core, I^2C, SAP, TPR	*csb_clk*	Off, *csb_clk*, *csb_clk*/2, *csb_clk*/3
USB DR	*csb_clk*	Off, *csb_clk*, *csb_clk*/2, *csb_clk*/3
PCI and DMA complex	*csb_clk*	Off, *csb_clk*

This table provides the operating frequencies for the MPC8313E TEPBGAII under recommended operating conditions (see Table 2).

Table 64. Operating Frequencies for TEPBGAII

Characteristic[1]	Maximum Operating Frequency	Unit
e300 core frequency (*core_clk*)	333	MHz
Coherent system bus frequency (*csb_clk*)	167	MHz
DDR1/2 memory bus frequency (MCK)[2]	167	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz
PCI input frequency (SYS_CLK_IN or PCI_CLK)	66	MHz

Note:

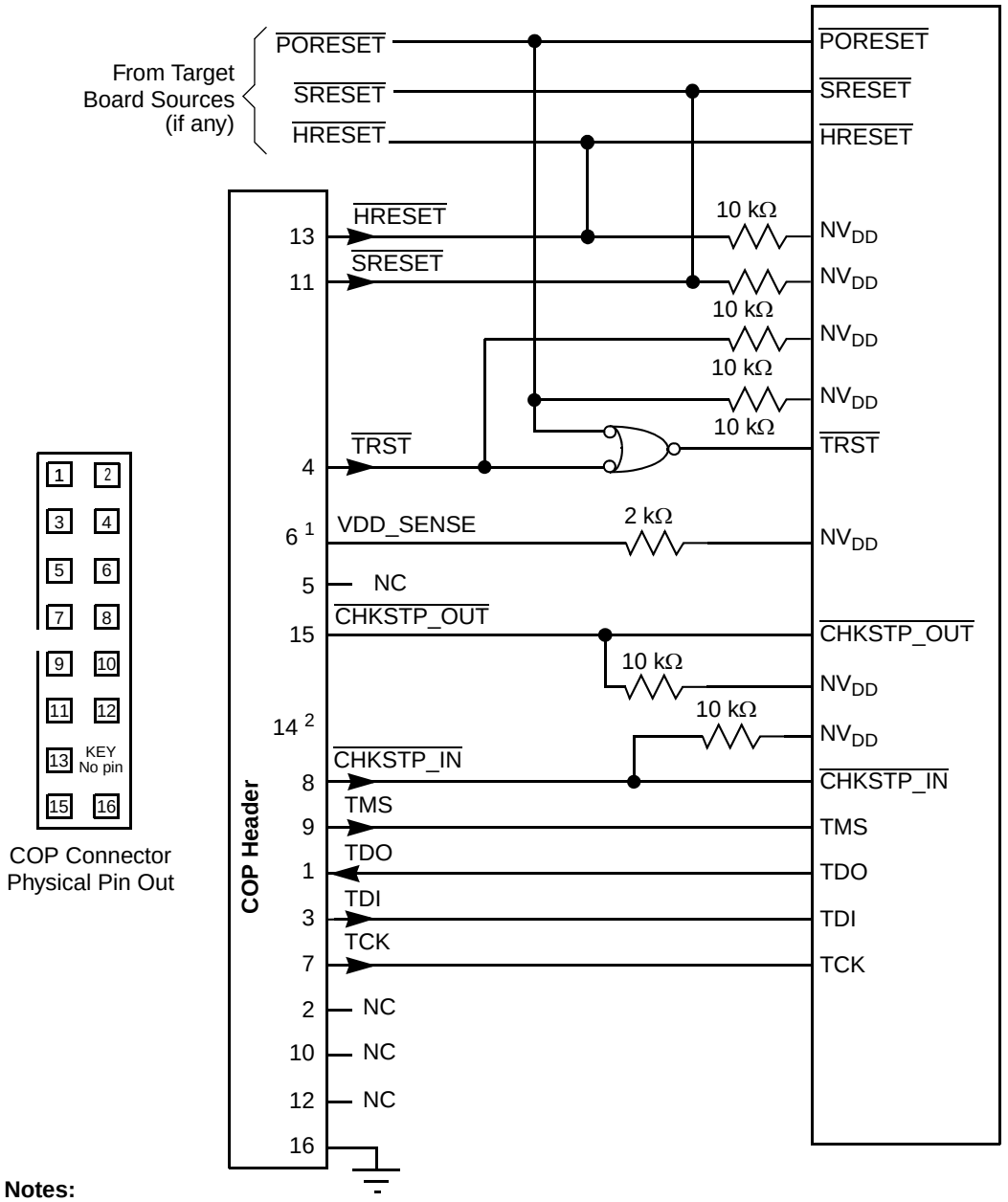
1. The SYS_CLK_IN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCK, LCLK[0:1], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM] and SCCR[USBDRCM] must be programmed such that the maximum internal operating frequency of the security core and USB modules do not exceed their respective value listed in this table.
2. The DDR data rate is 2x the DDR memory bus frequency.
3. The local bus frequency is 1/2, 1/4, or 1/8 of the *lbc_clk* frequency (depending on LCRR[CLKDIV]), which is in turn, 1x or 2x the *csb_clk* frequency (depending on RCWL[LBCM]).

20.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. This table shows the multiplication factor encodings for the system PLL.

Table 65. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3



Notes:
1. Some systems require power to be fed from the application board into the debugger repeater card via the COP header. In this case the resistor value for VDD_SENSE should be around 20 Ω.
2. Key location; pin 14 is not physically present on the COP header.

Figure 61. JTAG Interface Connection

23 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 23.1, “Part Numbers Fully Addressed by this Document.”

24 Revision History

This table summarizes a revision history for this document.

Table 73. Document Revision History

Rev. Number	Date	Substantive Change(s)
4	11/2011	• In Table 2, added following notes: – Note 3: Min temperature is specified with T_A; Max temperature is specified with T_J – Note 4: All Power rails must be connected and power applied to the MPC8313 even if the IP interfaces are not used. – Note 5: All I/O pins should be interfaced with peripherals operating at same voltage level. – Note 6: This voltage is the input to the filter discussed in Section 22.2, “PLL Power Supply Filtering.” and not necessarily the voltage at the AVDD pin, which may be reduced from VDD by the filter • Decoupled PCI_CLK and SYS_CLK_IN rise and fall times in Table 8. Relaxed maximum rise/fall time of SYS_CLK_IN to 4ns. • Added a note in Table 27 stating “The frequency of RX_CLK should not exceed the TX_CLK by more than 300 ppm." • In Table 30: – Changed max value of t_{skrgt} in “Data to clock input skew (at receiver)” row from 2.8 to 2.6. – Added Note 7, stating that, “The frequency of RX_CLK should not exceed the GTX_CLK125 by more than 300 ppm.” • Added a note stating “eTSEC should be interfaced with peripheral operating at same voltage level” in Section 8.1.1, “TSEC DC Electrical Characteristics.” • TSEC1_MDC and TSEC_MDIO are powered at 3.3V by NVDD. Replaced LVDDA/LVDDB with NVDD and removed instances of 2.5V at several places in Section 8.5, “Ethernet Management Interface Electrical Characteristics.” • In Table 43, changed min/max values of t_{CLK_TOL} from 0.05 to 0.005. • In Table 62: – Added Note 2 for LGPL4 in showing LGPL4 as open-drain. – Removed Note 2 from TSEC1_MDIO. – Added Note 10: This pin has an internal pull-up. – Added Note 11: This pin has an internal pull-down. – Added Note 12: “In MII mode, GTX_CLK should be pulled down by 300 Ω to V_{SS}” to TSEC1_GTX_CLK and TSEC2_GTX_CLK. • In Section 19.1, “Package Parameters for the MPC8313E TEPBGAII,” replaced "5.5 Sn/0.5 Cu/4 Ag" with "Sn/3.5 Ag." • Added foot note 3 in Table 65 stating “The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz.” • In Table 72: – Added AD = 266 and D = 266. – Added “C = 2.2” in “Revision level” column. – Added Note 4. • Changed resitor from 1.0 Ω to 10 Ω in Figure 58. • Replaced LCCR with LCRR throughout. • Added high-speed to USB Phy description.
3	01/2009	• Table 72, in column aa, changed to AG = 400 MHz.
2.2	12/2008	• Made cross-references active for sections, figures, and tables.
2.1	12/2008	• Added Figure 2, after Table 2 and renumbered the following figures.

Table 73. Document Revision History (continued)

Rev. Number	Date	Substantive Change(s)
2	10/2008	• Added Note “The information in this document is accurate for revision 1.0, and 2.x and later. See Section 24.1, “Part Numbers Fully Addressed by this Document,” before Section 1, “Overview.” • Added part numbering details for all the silicon revisions in Table 74. • Changed V_{IH} from 2.7 V to 2.4 V in Table 7. • Added a row for V_{IH} level for Rev 2.x or later in Table 45. • Added a column for maximum power dissipation in low power mode for Rev 2.x or later silicon in Table 6. • Added a column for Power Nos for Rev 2.x or later silicon and added a row for 400 MHz in Table 4. • Removed footnote, “These are preliminary estimates.” from Table 4. • Added Table 21 for DDR AC Specs on Rev 2.x or later silicon. • Added Section 9, “High-Speed Serial Interfaces (HSSI).” • Added $\overline{\text{LFWE}}$, LFCLE, LFALE, $\overline{\text{LOE}}$, $\overline{\text{LFRE}}$, $\overline{\text{LFWP}}$, $\overline{\text{LGTA}}$, LUPWAIT, and $\overline{\text{LFRB}}$ in Table 63. • In Table 39, added note 2: “This parameter is dependent on the csb_clk speed. (The MIIMCFG[Mgmt Clock Select] field determines the clock frequency of the Mgmt Clock EC_MDC.)” • Removed mentions of SGMII (SGMII has separate specs) from Section 8.1, “Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RMII/RGMII/SGMII/RTBI Electrical Characteristics.” • Corrected Section 8.1, “Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RMII/RGMII/SGMII/RTBI Electrical Characteristics,” to state that RGMII/RTBI interfaces only operate at 2.5 V, not 3.3 V. • Added ZQ package to ordering information In Table 74 and Section 19.1, “Package Parameters for the MPC8313E TEPBGAII” (applicable to both silicon rev. 1.0 and 2.1) • Removed footnotes 5 and 6 from Table 1 (left over when the PCI undershoot/overshoot voltages and maximum AC waveforms were removed from Section 2.1.2, “Power Supply Voltage Specification”). • Removed SD_PLL_TPD (T2) and SD_PLL_TPA_ANA (R4) from Table 63. • Added Section 8.3, “SGMII Interface Electrical Characteristics.” Removed Section 8.5.3 SGMII DC Electrical Characteristics. • Removed “HRESET negation to SRESET negation (output)” spec and changed “HRESET/SRESET assertion (output)” spec to “HRESET assertion (output)” in Table 10. • Clarified POR configuration signal specs to “Time for the device to turn off POR configuration signal drivers with respect to the assertion of HRESET” and “Time for the device to turn on POR configuration signal drivers with respect to the negation of HRESET” in Table 10. • Added Section 24.2, “Part Marking,” and Figure 62.